

PSMN8R5-100ES

N-channel 100 V 8.5 mΩ standard level MOSFET in I2PAK
11 October 2012 Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- AC-to-DC power supply equipment
- Motor control
- Server power supplies
- Synchronous rectification

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	T _j = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	263	W
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 13; Fig. 12		-	6.4	8.5	mΩ
Dynamic ch	aracteristics						
Q_{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 50 V;		-	33	-	nC
Q _{G(tot)}	total gate charge	Fig. 14; Fig. 15		-	111	-	nC
Avalanche I	Ruggedness		'	'			
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 100 V; R_{GS} = 50 Ω; unclamped; Fig. 3		-	-	219	mJ

[1] Continious current limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain		
3	S	source		G T T
mb	D	mounting base; connected to drain		mbb076 S
			I2PAK (SOT226)	

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN8R5-100ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226		

4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN8R5-100ES	PSMN8R5-100ES

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	100	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 1</u>	[1]	-	100	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>		-	75	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; Fig. 4		-	429	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	263	W
T _{stg}	storage temperature			-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dra	in diode					,
I _S	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	429	Α
Avalanche	Ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_{D} = 100 A; $V_{sup} \le$ 100 V; R_{GS} = 50 Ω; unclamped; Fig. 3		-	219	mJ

[1] Continious current limited by package.

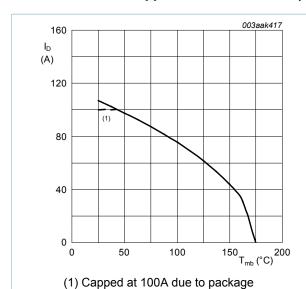


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$

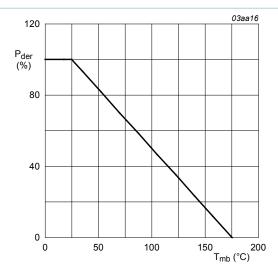


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

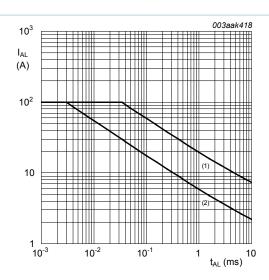


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1)
$$T_{j (init)} = 25$$
°C; (2) $T_{j (init)} = 130$ °C

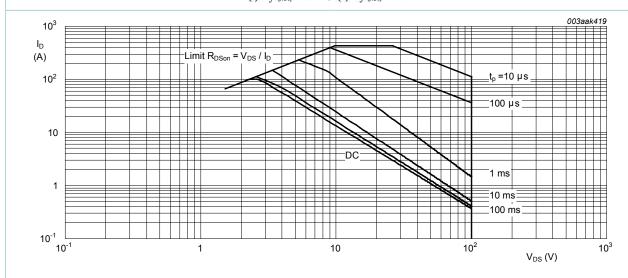


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

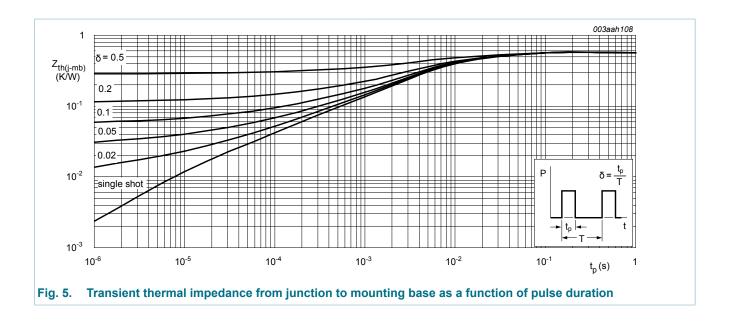
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	0.49	0.57	K/W	

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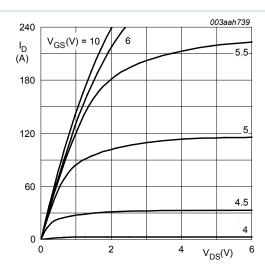


7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	100	-	-	V
	breakdown voltage	I_D = 250 μ A; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11	2.4	3	4	V
V_{GSth}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 100 °C	-	-	20	μΑ
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12	-	-	22.6	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 12	-	-	14.9	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 13; Fig. 12	-	6.4	8.5	mΩ
R_G	gate resistance	f = 1 MHz	-	0.71	-	Ω

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V;	-	111	-	nC
Q _{GS}	gate-source charge	Fig. 14; Fig. 15	-	24	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	16	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	8	-	nC
Q_{GD}	gate-drain charge		-	33	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 15 A; V _{DS} = 50 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	4.4	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 16; Fig. 17$	-	5512	-	pF
C _{oss}	output capacitance	V_{DS} = 50 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 16	-	380	-	pF
C _{rss}	reverse transfer capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 16; Fig. 17$	-	256	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 50 V; R _L = 2 Ω; V _{GS} = 10 V;	-	20	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	35	-	ns
t _{d(off)}	turn-off delay time		-	87	-	ns
t _f	fall time		-	43	-	ns
Source-drai	in diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 18$	-	0.82	1.2	V
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V;	-	53	-	ns
Q _r	recovered charge	V _{DS} = 50 V	-	124	-	nC



 $T_j = 25 \, ^{\circ}C; t_p = 300 \, \mu s$

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

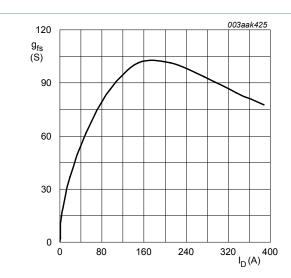


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25^{\circ}C; \ V_{DS} = 10V$$

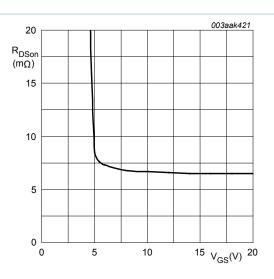


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

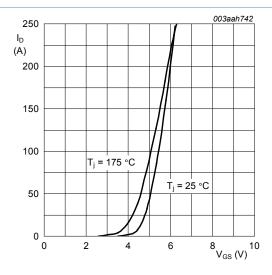


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

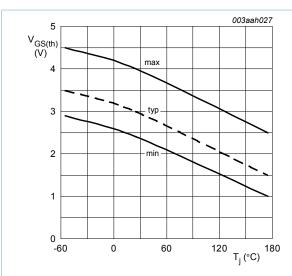


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

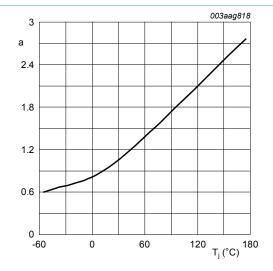


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$\mathbf{a} = \frac{R_{DSon}}{R_{DSon(25 \text{ CC})}}$$

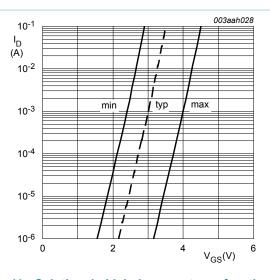


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

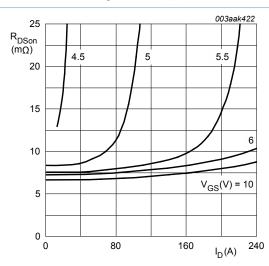


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

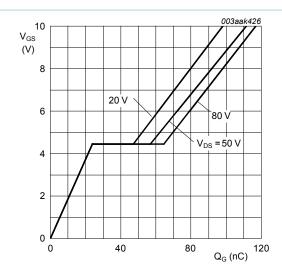
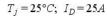


Fig. 14. Gate-source voltage as a function of gate charge; typical values



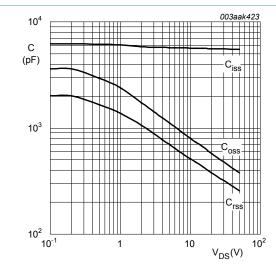


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Input and reverse transfer capacitances as a as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

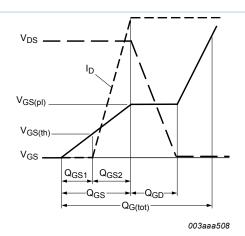
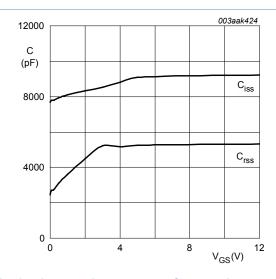


Fig. 15. Gate charge waveform definitions



function of gate-source voltage, typical values

$$\mathbf{f} = \mathbf{1}$$
 MHz; $V_{DS} = \mathbf{0}$ V

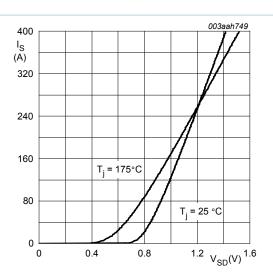


Fig. 18. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

8. Package outline

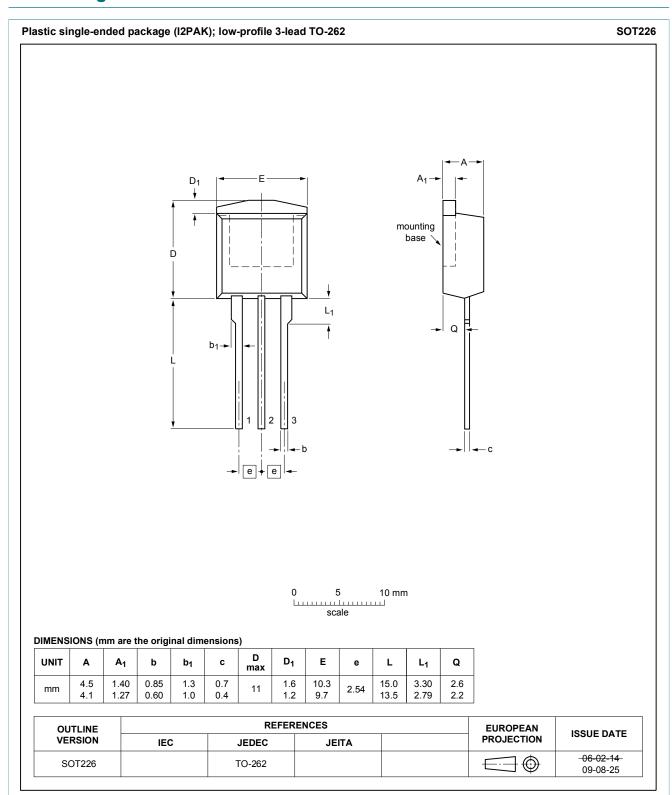


Fig. 19. Package outline I2PAK (SOT226)

9. Legal information

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